

Date:- 18 Dec, 2001

Data Sheet Issue:- 1

# Phase Control Thyristor Types N0882NC400 to N0882NC450

# **Absolute Maximum Ratings**

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
$V_{DRM}$	Repetitive peak off-state voltage, (note 1)	4000-4500	V
$V_{DSM}$	Non-repetitive peak off-state voltage, (note 1)	4000-4500	V
$V_{RRM}$	Repetitive peak reverse voltage, (note 1)	4000-4500	V
$V_{RSM}$	Non-repetitive peak reverse voltage, (note 1)	4100-4600	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
I <sub>T(AV)</sub>	Mean on-state current. T <sub>sink</sub> =55℃, (note 2)	882	Α
I <sub>T(AV)</sub>	Mean on-state current. T <sub>sink</sub> =85℃, (note 2)	616	Α
I <sub>T(AV)</sub>	Mean on-state current. T <sub>sink</sub> =85℃, (note 3)	383	Α
I <sub>T(RMS)</sub>	Nominal RMS on-state current. T <sub>sink</sub> =25℃, (note 2)	1724	Α
I <sub>T(d.c.)</sub>	D.C. on-state current. T <sub>sink</sub> =25℃, (note 4)	1536	Α
I <sub>TSM</sub>	Peak non-repetitive surge t <sub>p</sub> =10ms, V <sub>rm</sub> =0.6V <sub>RRM</sub> , (note 5)	7700	А
I <sub>TSM2</sub>	Peak non-repetitive surge t <sub>p</sub> =10ms, V <sub>rm</sub> ≤10V, (note 5)	8470	Α
l <sup>2</sup> t	$I^2$ t capacity for fusing $t_p$ =10ms, $V_{rm}$ =0.6 $V_{RRM}$ , (note 5)	296×10 <sup>3</sup>	A <sup>2</sup> s
l <sup>2</sup> t	I <sup>2</sup> t capacity for fusing t <sub>p</sub> =10ms, V <sub>rm</sub> ≤10V, (note 5)	359×10 <sup>3</sup>	A <sup>2</sup> s
d: /d+	Maximum rate of rise of on-state current (repetitive), (Note 6)	150	A/µs
di <sub>⊤</sub> /dt	Maximum rate of rise of on-state current (non-repetitive), (Note 6)	300	A/µs
$V_{RGM}$	Peak reverse gate voltage	5	V
P <sub>G(AV)</sub>	Mean forward gate power	4	W
P <sub>GM</sub>	Peak forward gate power	30	W
$V_{GD}$	Non-trigger gate voltage, (Note 7)	0.25	V
T <sub>HS</sub>	Operating temperature range	-40 to +125	C
T <sub>stg</sub>	Storage temperature range	-40 to +150	${\mathcal C}$

#### Notes:

- 1) De-rating factor of 0.13% per  $\mathbb C$  is applicable for  $T_j$  below 25 $\mathbb C$ .
- 2) Double side cooled, single phase; 50Hz, 180° half-sinewave.
- 3) Single side cooled, single phase; 50Hz, 180° half-sinewave.
- 4) Double side cooled.
- 5) Half-sinewave, 125℃ T<sub>i</sub> initial.
- 6)  $V_D$ =67%  $V_{DRM}$ ,  $I_{TM}$ =500Å,  $I_{FG}$ =1Å,  $t_r$ ≤0.5 $\mu$ s,  $T_{case}$ =125°C.
- 7) Rated V<sub>DRM</sub>.

# **Characteristics**

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
$V_{TM}$	Maximum peak on-state voltage	-	-	2.98	I <sub>TM</sub> =1830A	V
$V_0$	Threshold voltage	-	-	1.30		V
rs	Slope resistance	-	-	0.92		mΩ
dv/dt	Critical rate of rise of off-state voltage	1000	-	-	V <sub>D</sub> =80% V <sub>DRM</sub> , linear ramp, gate o/c	V/μs
$I_{DRM}$	Peak off-state current	-	-	100	Rated V <sub>DRM</sub>	mA
I <sub>RRM</sub>	Peak reverse current	-	-	100	Rated V <sub>RRM</sub>	mA
V <sub>G</sub> T	Gate trigger voltage	-	-	3.0	T 05% V 40V L 04	V
$I_{GT}$	Gate trigger current	-	-	300	$T_j=25$ °C, V <sub>D</sub> =10V, I <sub>T</sub> =2A	mA
I <sub>H</sub>	Holding current	-	-	1.0	T <sub>j</sub> =25℃	Α
t <sub>gd</sub>	Gate controlled turn-on delay time	-	0.6	1.4	V <sub>D</sub> =80%V <sub>DRM</sub> , I <sub>TM</sub> =1000A, di/dt=10A/µs,	μs
t <sub>gt</sub>	Turn-on time	-	2.8	4.0	I <sub>FG</sub> =2A, t <sub>r</sub> =0.5μs, T <sub>j</sub> =25℃	
Qrr	Recovered Charge	-	4700	-		μC
Q <sub>ra</sub>	Recovered Charge, 50% chord	-	1700	2200	I <sub>TM</sub> =1000A, t <sub>p</sub> =1000μs, di/dt=10A/μs,	μC
I <sub>rm</sub>	Reverse recovery current	-	100	-	V <sub>r</sub> =50V	Α
t <sub>rr</sub>	Reverse recovery time, 50% chord	-	30	-		μs
	Turn-off time	-	700	850	$I_{TM}$ =1000A, $t_p$ =1000 $\mu$ s, $di/dt$ =10A/ $\mu$ s, $V_r$ =50V, $V_{dr}$ =80% $V_{DRM}$ , $dV_{dr}/dt$ =20V/ $\mu$ s	
tq	Turn-on time	-	1075	1200	$I_{TM}$ =1000A, $t_p$ =1000 $\mu$ s, $di/dt$ =10A/ $\mu$ s, $V_r$ =50V, $V_{dr}$ =80% $V_{DRM}$ , $dV_{dr}/dt$ =200V/ $\mu$ s	μs
D	Thermal registance, junction to heateink	-	-	0.024	Double side cooled	K/W
R <sub>th(j-hs)</sub>	Thermal resistance, junction to heatsink		-	0.048	Single side cooled	K/W
F	Mounting force	19	-	26		kN
$W_t$	Weight		510			g

Notes: -

1) Unless otherwise indicated T<sub>j</sub>=125°C.

# **Notes on Ratings and Characteristics**

# 1.0 Voltage Grade Table

Voltage Grade	V <sub>DRM</sub> V <sub>DSM</sub> V <sub>RRM</sub> V	V <sub>RSM</sub> V	V <sub>D</sub> V <sub>R</sub> DC V
40	4000	4100	2000
42	4200	4300	2040
44	4400	4500	2080
45	4500	4600	2100

# 2.0 Extension of Voltage Grades

This report is applicable to other and higher voltage grades when supply has been agreed by Sales/Production.

#### 3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/℃ is applicable to this device for T<sub>i</sub> below 25℃.

#### 4.0 Repetitive dv/dt

Standard dv/dt is 1000V/µs.

#### 5.0 Rate of rise of on-state current

The maximum un-primed rate of rise of on-state current must not exceed 300A/µs at any time during turnon on a non-repetitive basis. For repetitive performance, the on-state rate of rise of current must not exceed 150A/µs at any time during turn-on. Note that these values of rate of rise of current apply to the total device current including that from any local snubber network.

# 6.0 Gate Drive

The recommended pulse gate drive is 30V,  $30\Omega$  with a short-circuit current rise time of not more than 0.5 $\mu$ s. This gate drive must be applied when using the full di/dt capability of the device.

The pulse duration may need to be configured according to the application but should be no shorter than 20µs, otherwise an increase in pulse current may be needed to supply the necessary charge to trigger.

### 7.0 Computer Modelling Parameters

## 7.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_0 + \sqrt{{V_0}^2 + 4 \cdot f\!f^2 \cdot r_s \cdot W_{AV}}}{2 \cdot f\!f^2 \cdot r_s} \qquad W_{AV} = \frac{\Delta T}{R_{th}}$$
 and: 
$$\Delta T = T_{j\,\mathrm{max}} - T_{Hs}$$

Where  $V_0=1.30V$ ,  $r_s=0.92m\Omega$ ,

 $R_{th}$  = Supplementary thermal impedance, see table below.

ff = Form factor, see table below.

Supplementary Thermal Impedance							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave Double Side Cooled	0.03047	0.03035	0.02857	0.02733	0.02569	0.0242	0.024
Square wave Single Side Cooled	0.05823	0.0577	0.05408	0.05286	0.05121	0.0497	0.048
Sine wave Double Side Cooled	0.0303	0.0275	0.0262	0.02524	0.024		
Sine wave Single Side Cooled	0.05588	0.05323	0.05186	0.05089	0.048		

Form Factors							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave	3.46	2.45	2	1.73	1.41	1.15	1
Sine wave	3.98	2.78	2.22	1.88	1.57		

# 7.2 Calculating V<sub>T</sub> using ABCD Coefficients

The on-state characteristic I<sub>T</sub> vs. V<sub>T</sub>, on page 5 is represented in two ways;

- the well established V<sub>0</sub> and r<sub>s</sub> tangent used for rating purposes and
- a set of constants A, B, C, D, forming the coefficients of the representative equation for V<sub>T</sub> in (ii) terms of I<sub>T</sub> given below:

$$V_T = A + B \cdot \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for V<sub>T</sub> agree with the true device characteristic over a current range, which is limited to that plotted.

25℃ Coefficients		125℃ Coefficients	
Α	1.309129	Α	0.127546953
В	0.03313115	В	0.3431981
С	4.240333x10 <sup>-4</sup>	С	1.363618 x10 <sup>-3</sup>
D	4.47 x10 <sup>-3</sup>	D	-0.05192086

# 7.3 D.C. Thermal Impedance Calculation

$$r_{t} = \sum_{p=1}^{p=n} r_{p} \cdot \left(1 - e^{\frac{-t}{\tau_{p}}}\right)$$

Where p = 1 to n, n is the number of terms in the series and:

t = Duration of heating pulse in seconds.

r, = Thermal resistance at time t.

 $r_p$  = Amplitude of  $p_{th}$  term.

 $\tau_p$  = Time Constant of  $r_{th}$  term.

D.C. Single Side Cooled							
Term	Term 1 2 3 4						
$r_p$	0.02852028	6.529239x10 <sup>-3</sup>	9.588999×10 <sup>-3</sup>	4.395357x10 <sup>-3</sup>			
$ au_{ ho}$	6.388123	3.301838	0.2277620	12.95898x10 <sup>-3</sup>			

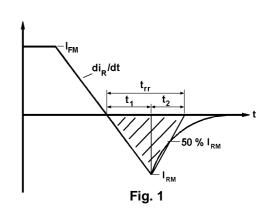
D.C. Double Side Cooled							
Term	Term 1 2 3 4 5						
$r_p$	0.01258158	5.616905x10 <sup>-3</sup>	2.450566x10 <sup>-3</sup>	2.454577x10 <sup>-3</sup>	0.2714915x10 <sup>-3</sup>		
$ au_{ ho}$	0.9103414	0.1399022	50.86435x10 <sup>-3</sup>	9.193607x10 <sup>-3</sup>	2.357793x10 <sup>-3</sup>		

#### 8.0 Reverse recovery ratings

- (i)  $Q_{ra}$  is based on 50%  $I_{rm}$  chord as shown in Fig. 1.
- (ii)  $Q_{rr}$  is based on a 150 $\mu s$  integration time.

i.e. 
$$Q_{rr} = \int_{0}^{150 \,\mu s} i_{rr}.dt$$
$$K \ Factor = \frac{t1}{t2}$$

(iii) 
$$K Factor = \frac{t1}{t2}$$



## **Curves**

Figure 1 - On-state characteristics of Limit device

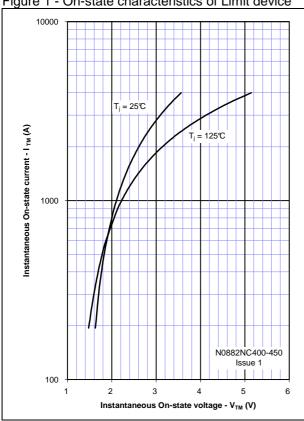


Figure 2 - Transient Thermal Impedance

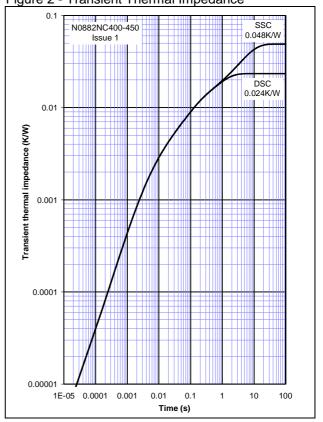


Figure 3 - Gate Characteristics – Trigger Limits

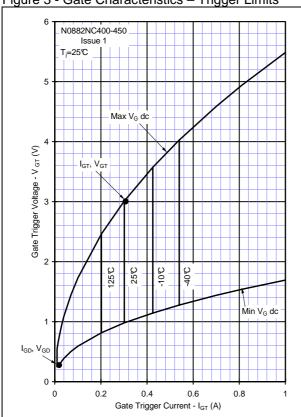
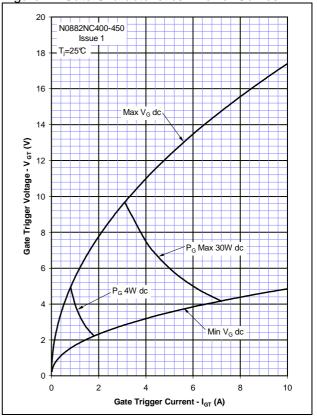


Figure 4 - Gate Characteristics - Power Curves





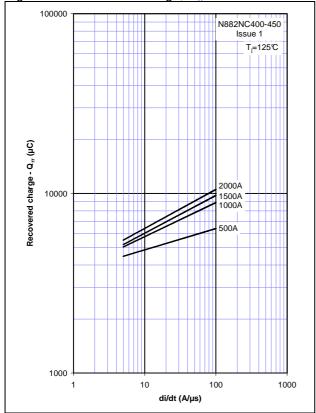


Figure 6 – Recovered charge, Q<sub>ra</sub> (50% chord)

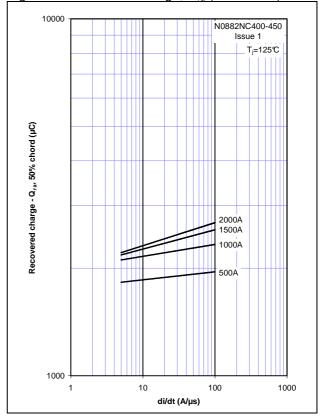


Figure 7 - Reverse recovery current, I<sub>rm</sub>

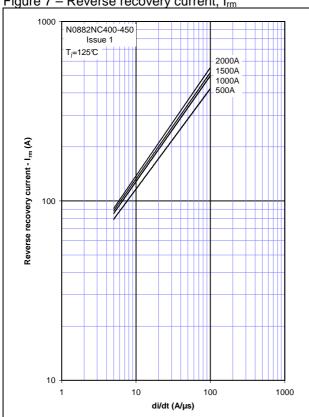


Figure 8 – Reverse recovery time, t<sub>rr</sub> (50% chord)

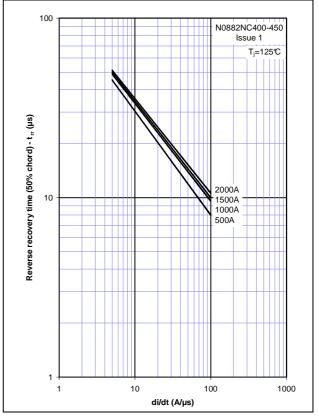


Figure 9 – On-state current vs. Power dissipation – Double Side Cooled (Sine wave)

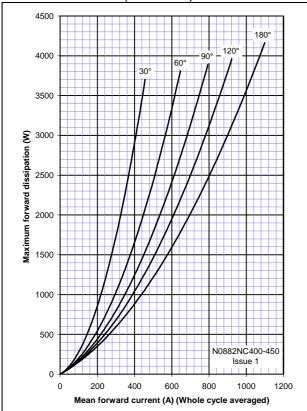


Figure 10 – On-state current vs. Heatsink temperature - Double Side Cooled (Sine wave)

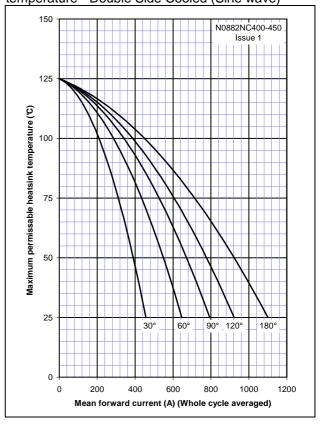


Figure 11 – On-state current vs. Power dissipation – Double Side Cooled (Square wave)

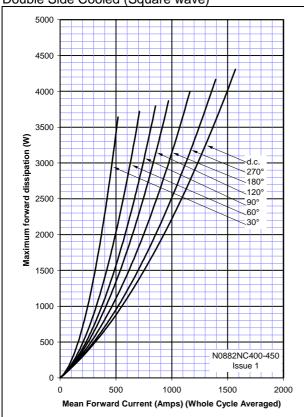


Figure 12 – On-state current vs. Heatsink temperature - Double Side Cooled (Square wave)

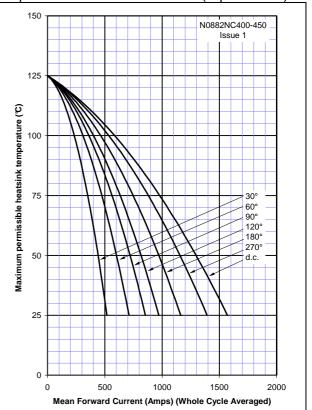


Figure 13 – On-state current vs. Power dissipation – Single Side Cooled (Sine wave)

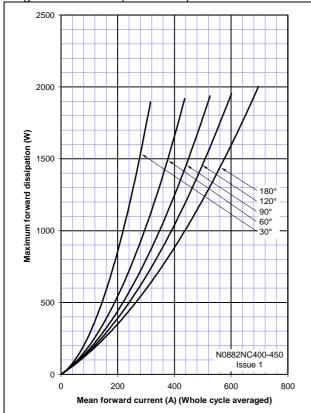


Figure 14 – On-state current vs. Heatsink temperature - Single Side Cooled (Sine wave)

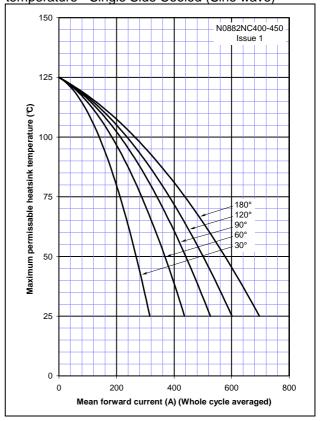


Figure 15 – On-state current vs. Power dissipation – Single Side Cooled (Square wave)

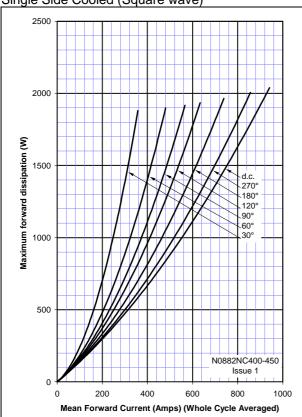
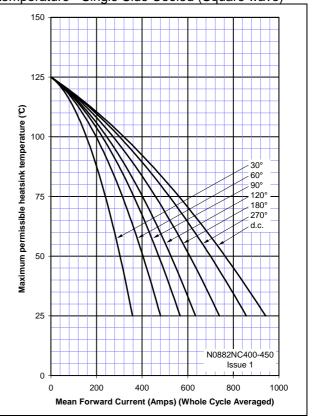
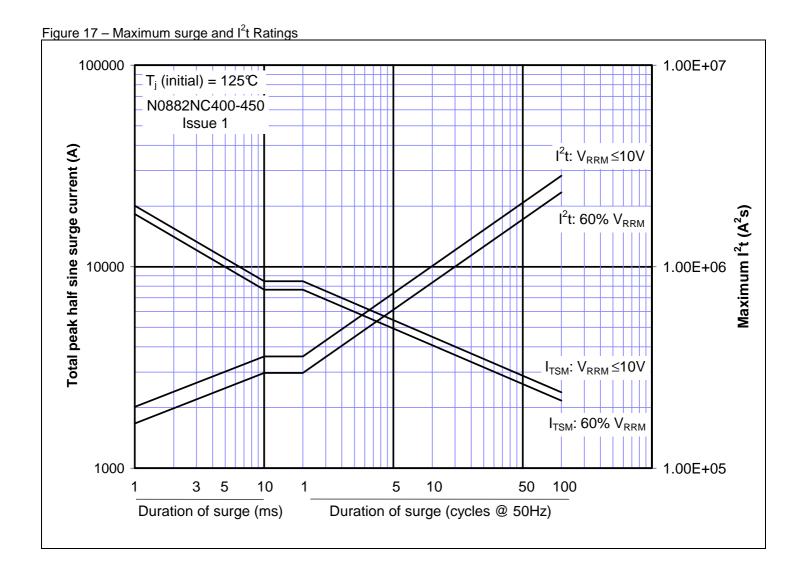
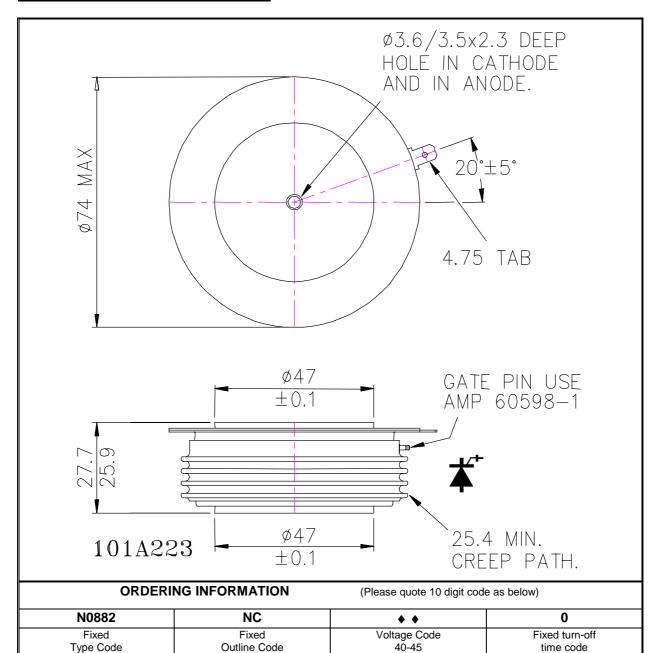


Figure 16 – On-state current vs. Heatsink temperature - Single Side Cooled (Square wave)





# **Outline Drawing & Ordering Information**





UK: Westcode Semiconductors Ltd.
P.O. Box 57, Chippenham, Wiltshire, England. SN15 1JL.
Tel: +44 (0) 1249 444524 Fax: +44 (0) 1249 659448
E-Mail: WSL.sales@westcode.com

USA: Westcode Semiconductors Inc. 3270 Cherry Avenue, Long Beach, California 90807 Tel: +1 (562) 595 6971 Fax: +1 (562) 595 8182 E-Mail: WSI.sales@westcode.com

Internet: http://www.westcode.com

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